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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: T. FRANK WANG

ART UNIT: 1765

SERIAL NO.: 09/609,387

EXAMINER: PEREZ, R.

FILING DATE: JULY 3, 2000

FOR: METHOD OF UNIFORMLY ETCHING REFRactory METALS,  
REFRACTORY METAL ALLOYS AND REFRACTORY METAL  
SILICIDES

**AMENDMENT**

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Responsive to the outstanding Office Action issued July 23, 2002 in the above-captioned matter, entry of the following amendments is respectfully requested.

**IN THE CLAIMS**

Please amend the claims as follows:

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1. A method for etching a semiconductor device to form an etched pattern therein, comprising:
- (a) providing a semiconductor device having a plurality of layers, at least one of the layers of the semiconductor device comprising a refractory metal-containing material; and
- (b) etching the semiconductor device under conditions with an etchant composition comprising a first etchant chemistry which comprises a chlorine source free of  $BCl_3$  and a second etchant chemistry which is free of fluorine
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15. A method of etching a refractory metal-containing layer and an oxide layer, the method comprising:
- (a) etching the refractory metal-containing layer to an end point using a first etchant

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